IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Alfred Haeusler et al.

Art Unit:

2812

Serial No.:

10/824,745

Examiner:

TBD

Filed:

04/15/2004

Docket No.: TID-34858

Customer No.: 23494

Conf. No.:

7054

For: METHOD OF FABRICATING AN INTEGRATED SILICON-GERMANIUM HETEROBIPOLAR TRANSISTOR AND AN INTEGRATED SILICON-GERMANIUM

HETEROBIPOLAR TRANSISTOR

ART CITE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. =1.8(a) I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-

Marianna Smith

Dear Sir:

Please make the references listed on the enclosed PTO-1449 of record under 37 C.F.R. 1.56, 1.97, and 1.98 in the patent application identified above. They were cited in a corresponding German patent application. Copies of the listed references are enclosed.

Respectfully submitted,

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FAX: (972)917-4418 (972)917-4417

OIPE		Complete If Known		
		Application Number	10/824,745	
(2001 1)		Filing Date	4/15/2004	
(MIE 3 0 5004 A		First Named Inventor	Alfred Haeusler	
		Group Art Unit	2812	
		Examiner Name	TBD.	
Sheet 1 PADEWOOF	1	Attorney Docket No.	TID-34858	

	U.S. PATENT DOCUMENTS							
	Cite No.1	U.S. Patent Document		Name of Patentee	Date of Pub.			
Exam. Initials*		Number	Kind Code ² (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figure Appear		
	AA	4,672,413		Gardner	6/9/1987			
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
	AJj							
	AK							

	FOREIGN PATENT DOCUMENTS							
Exam. Initials*	Cite No.1	Foreign Patent Document			Name of	Date of Pub.		
		Office ³	Number⁴	Kind Code ² (if known)	Patentee or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T⁵
	ВА	PCT	WO 02/41361 A2		Joshi et al.	5/23/2002		
	BB	DE	197 52 052 A1		Sanders et al.	8/6/1998		
	вс	DE	690 22 692 T2		Morishita	3/14/1996		
	BD							
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	BF							
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	OTHER PRIOR ARY - NON PATENT LITERATURE DOCUMENTS					
Exam. Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²			
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Other Prior Art/Non-Patent Literature Documents: ¹Unique citation designation number. ²Applicant is to place a check mark here if English Translation is attached.

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